

PLATING APPARATUS FOR SEMICONDUCTOR WAFER

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Abstract

PURPOSE:To form a metal as a wiring material on the semiconductor wafer surface by means of an electrolytic plating with a good performance, by providing a distribution correcting plate on the net-like member of an anode electrode opposing to the surface to be plated, and disposing a second positive electrode connected to the positive electrode in plating along the plating unit body.

CONSTITUTION:A reference numeral 21 denotes a plating unit body made of Teflon or the like, while a numeral 22 represents what is called a cathode electrode 22 which serves as the negative electrode in plating. A semiconductor wafer support 22a arranged to contact to the cathode electrode is formed into a needle-like shape under the necessity for supplying a plating current to the surface to be plated. A distribution correcting plate 27 (a disc bored in its center) made of an insulating material such as Teflon is installed on the upper surface of a net-like member 23a of an anode electrode 23. A second positive electrode (auxiliary electrode) 28 connected to the anode electrode 23 (having the same potential as the anode electrode) is installed along the inner wall of the plating unit body 21. A numeral 25 represents a semiconductor wafer having a part to be plated so that a plated wiring will be formed thereon, while a numeral 26 denotes each of arrows showing how a plating solution flows.

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